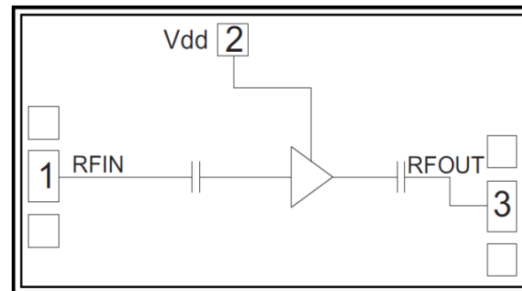


**Features**

- Single Biasing Voltage (Self Biased)
- Frequency: 17-23GHz
- Small Signal Gain: 26.5dB
- Noise Figure: 1.3dB typ./1.5dB max.
- P1dB: 4dBm
- Power Supply: +5V/12mA
- Input/Output: 50Ω
- Die Size: 1.85 x 1.25 x 0.09 mm

**Functional Block Diagram**

**Typical Applications**

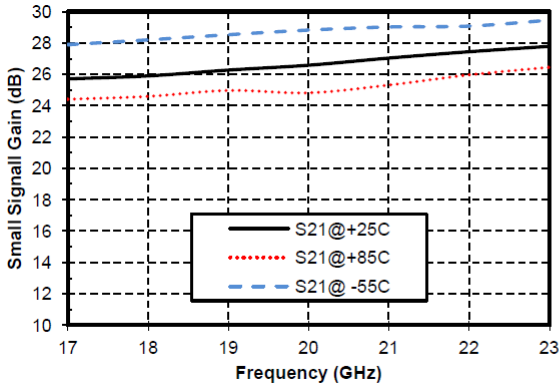
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

**Electrical Specifications**

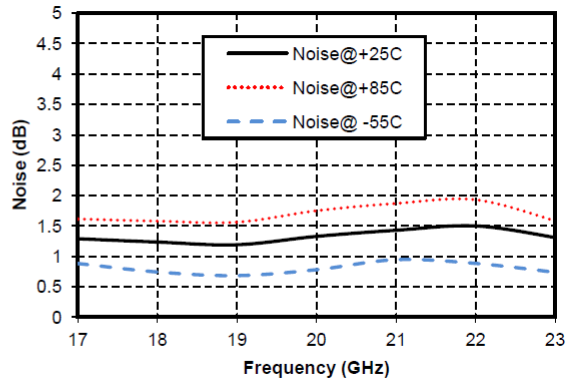
TA = +25°C, Vd = +5V

Parameters	Min.	Typ.	Max.	Units
<b>Frequency</b>	<b>17-23</b>			<b>GHz</b>
<b>Small Signal Gain</b>	<b>25.5</b>	<b>26.5</b>	<b>27.5</b>	<b>dB</b>
<b>Gain Flatness</b>		<b>±1.0</b>		<b>dB</b>
<b>Noise Figure</b>	<b>-</b>	<b>1.3</b>	<b>1.5</b>	<b>dB</b>
<b>Output 1dB Compression (P1dB)</b>	<b>3.5</b>	<b>4</b>	<b>4.5</b>	<b>dBm</b>
<b>Saturated Output Power (Psat)</b>	<b>4.5</b>	<b>5</b>	<b>6</b>	<b>dBm</b>
<b>Input Return Loss</b>	<b>14</b>	<b>20</b>	<b>-</b>	<b>dB</b>
<b>Output Return Loss</b>	<b>11</b>	<b>16</b>	<b>-</b>	<b>dB</b>
<b>Static current</b>		<b>12</b>		<b>mA</b>

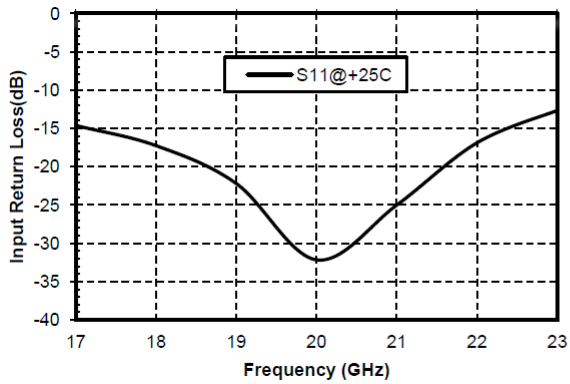
Gain vs. Frequency



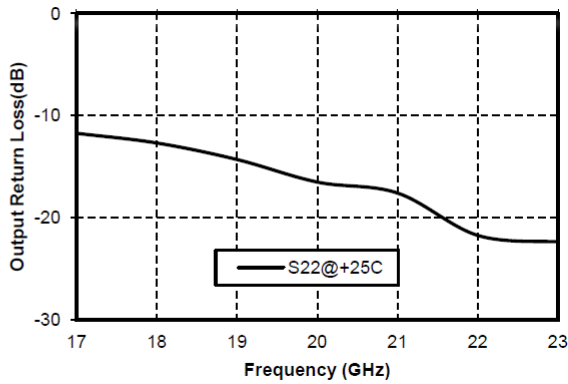
Noise Figure vs. Frequency



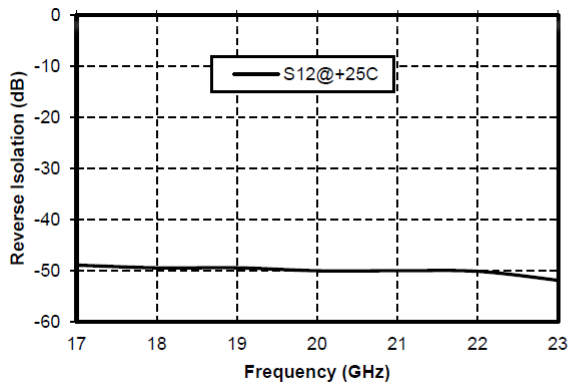
Input Return Loss vs. Frequency



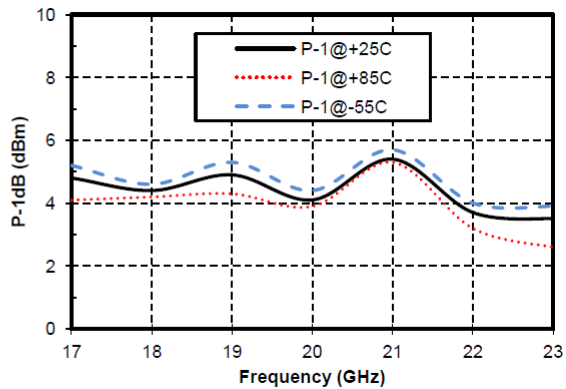
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

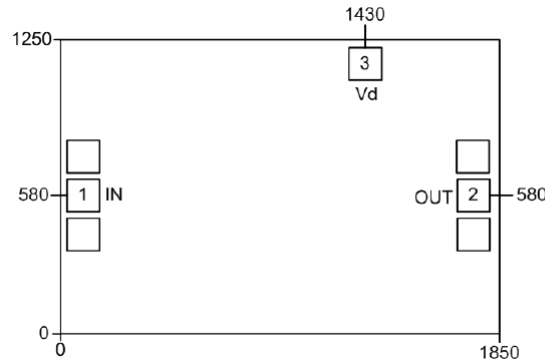


P1dB vs. Frequency





**Outline Drawing:**  
All Dimensions in  $\mu\text{m}$

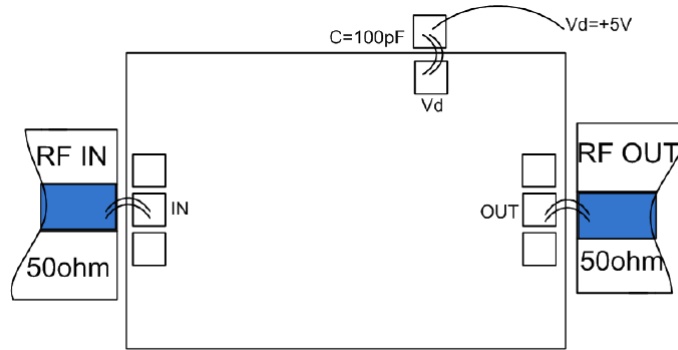


**Pad Description**

Pad	Function	Description	Equivalent Circuit
1	RF IN	RF signal input terminal, no blocking capacitor required.	
2	RF OUT	RF signal output terminal, no blocking capacitor required.	
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.	
Die bottom	GND	Die bottom must be connected to RF/DC ground.	



### Assembly Drawing



#### Notes:

1. Die thickness: 100um
2. Typical bond pad is 100\*100  $\mu\text{m}^2$
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

#### Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C